

ABSTRACT OF THE DISCLOSURE

A process for producing a semiconductor substrate is provided which comprises steps of forming a porous layer on a first substrate, forming a nonporous monocrystalline semiconductor layer on the porous layer of the first substrate, bonding the nonporous monocrystalline layer onto a second substrate, separating the bonded substrates at the porous layer, removing the porous layer on the second substrate, and removing the porous layer constituting the first substrate.

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